FQD10N20C / FQU10N20C

N-Channel QFET® MOSFET

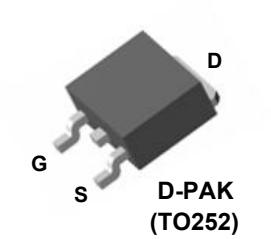
200 V, 7.8 A, 360 mΩ

Description

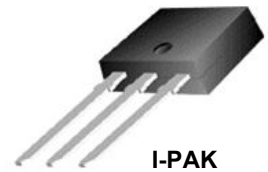
This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor®'s proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

- 7.8 A, 200 V, $R_{DS(on)}$ = 360 mΩ (Max.)@ V_{GS} = 10 V, I_D = 3.9 A
- Low Gate Charge (Typ. 20 nC)
- Low Crss (Typ. 40.5 pF)
- 100% Avalanche Tested



D-PAK
(TO252)



I-PAK
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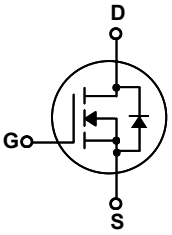

Absolute Maximum Ratings

T_C = 25°C unless otherwise noted

Symbol	Parameter		FQD10N20C / FQU10N20C	Unit
V_{DSS}	Drain-Source Voltage		200	V
I_D	Drain Current - Continuous (T_C = 25°C)		7.8	A
	- Continuous (T_C = 100°C)		5.0	A
I_{DM}	Drain Current - Pulsed	(Note 1)	31.2	A
V_{GSS}	Gate-Source Voltage		± 30	V
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	210	mJ
I_{AR}	Avalanche Current	(Note 1)	7.8	A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	5.0	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	5.5	V/ns
P_D	Power Dissipation (T_C = 25°C)		50	W
	- Derate above 25°C		0.4	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FQD10N20C / FQU10N20C	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient*	50	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	110	°C/W

* When mounted on the minimum pad size recommended (PCB Mount)

Electrical Characteristics

T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA	200	--	--	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	--	0.28	--	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 200 V, V_{GS} = 0 V	--	--	10	μA
		V_{DS} = 160 V, T_C = 125°C	--	--	100	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 30 V, V_{DS} = 0 V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30 V, V_{DS} = 0 V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 3.9 A	--	0.29	0.36	Ω
g_{FS}	Forward Transconductance	V_{DS} = 40 V, I_D = 3.9 A	--	5.6	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz	--	395	510	pF
C_{oss}	Output Capacitance		--	97	125	pF
C_{rss}	Reverse Transfer Capacitance		--	40.5	53	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 100 V, I_D = 9.5 A, R_G = 25 Ω (Note 4)	--	11	30	ns
t_r	Turn-On Rise Time		--	92	190	ns
$t_{d(off)}$	Turn-Off Delay Time		--	70	150	ns
t_f	Turn-Off Fall Time		--	72	160	ns
Q_g	Total Gate Charge	V_{DS} = 160 V, I_D = 9.5 A, V_{GS} = 10 V (Note 4)	--	20	26	nC
Q_{gs}	Gate-Source Charge		--	3.1	--	nC
Q_{gd}	Gate-Drain Charge		--	10.5	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	7.8	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	31.2	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 7.8 A	--	--	1.5	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_S = 9.5 A, dI_F / dt = 100 A/μs	--	158	--	ns
Q_{rr}	Reverse Recovery Charge		--	0.97	--	μC

Notes:
1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 5.2mH, I_{AS} = 7.8A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C
3. I_{SD} ≤ 9.5A, di/dt ≤ 300A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Essentially independent of operating temperature

Typical Characteristics

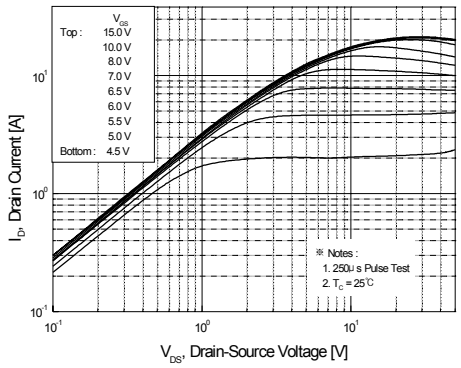

Figure 1. On-Region Characteristics

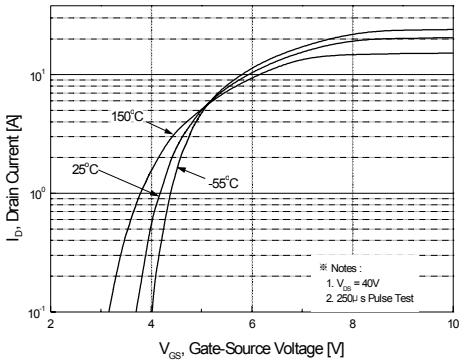

Figure 2. Transfer Characteristics

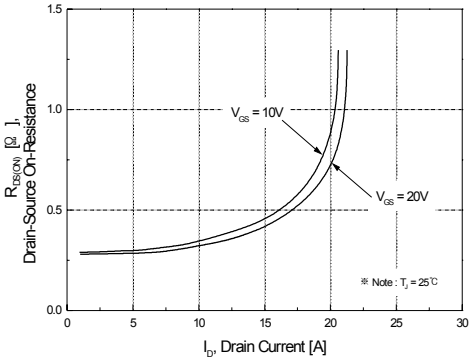

Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

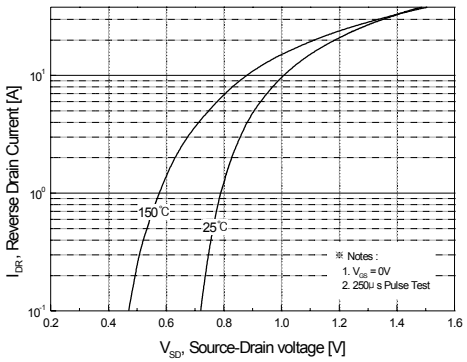

Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

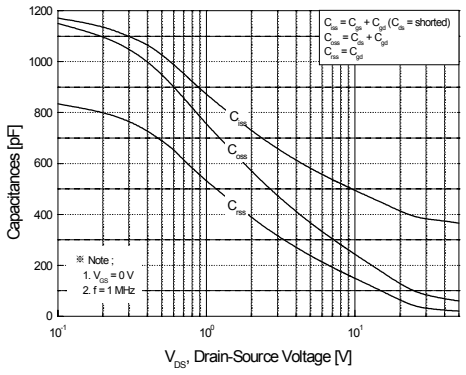

Figure 5. Capacitance Characteristics

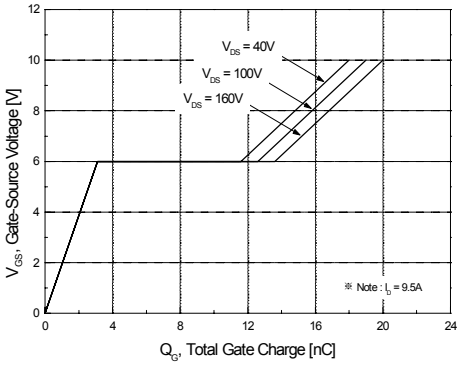

Figure 6. Gate Charge Characteristics